



# STD3NM60N

## N-channel 600 V, 1.6 $\Omega$ , 3.3 A, MDmesh™ II Power MOSFET in DPAK package

Datasheet — preliminary data

### Features

Order codes	V <sub>DSS</sub> @T <sub>J</sub> max	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STD3NM60N	650 V	< 1.8 $\Omega$	3.3 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

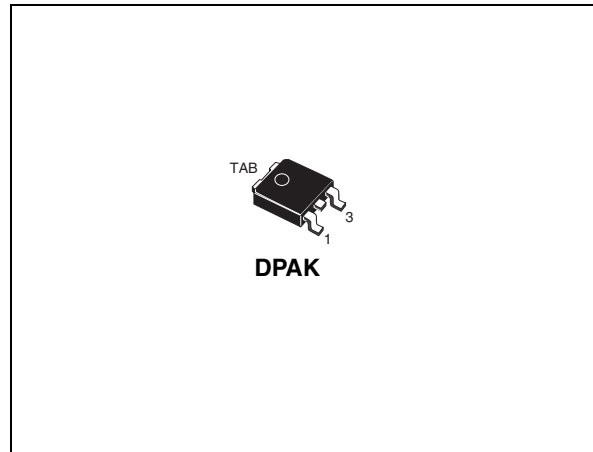


Figure 1. Internal schematic diagram

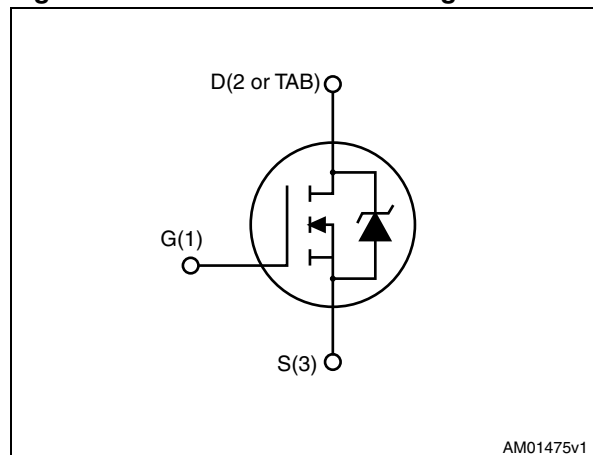


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD3NM60N	3NM60N	DPAK	Tape and reel

## Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate- source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	3.3	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	2.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	13	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	50	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$T_J$ $T_{stg}$	Operating junction temperature Storage temperature	- 55 to 150	$^\circ\text{C}$

1. Pulse width limited by safe operating area.

2.  $I_{SD} \leq 3.3\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DS\text{ peak}} \leq V_{(BR)DSS}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$ .

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max	50	$^\circ\text{C}/\text{W}$

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_J$ max)	1	A
EAS	Single pulse avalanche energy (starting $T_J=25\text{ }^\circ\text{C}$ , $I_D=I_{AR}$ , $V_{DD}=50\text{ V}$ )	86	mJ

## 2 Electrical characteristics

(T<sub>case</sub> = 25 °C unless otherwise specified)

**Table 5. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0	600			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = 600 V V <sub>DS</sub> = 600 V, T <sub>C</sub> = 125 °C			1 100	μA μA
I <sub>GSS</sub>	Gate-body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 25 V; V <sub>DS</sub> = 0			±100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static drain-source on-resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.65A		1.6	1.8	Ω

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C <sub>iss</sub>	Input capacitance	V <sub>DS</sub> = 50 V, f = 1 MHz, V <sub>GS</sub> = 0	-	188	-	pF
C <sub>oss</sub>	Output capacitance			12.8		pF
C <sub>rss</sub>	Reverse transfer capacitance			1.1		pF
C <sub>oss(tr)</sub> <sup>(1)</sup>	Output capacitance time related	V <sub>DS</sub> = 0, V <sub>GS</sub> = 0	-	96.8	-	pF
R <sub>g</sub>	Gate input resistance	f = 1 MHz open drain	-	6	-	Ω
Q <sub>g</sub>	Total gate charge	V <sub>DD</sub> = 480 V, I <sub>D</sub> = 3.3A, V <sub>GS</sub> = 10 V <i>(see Figure 15)</i>	-	9.5	-	nC
Q <sub>gs</sub>	Gate-source charge			2		nC
Q <sub>gd</sub>	Gate-drain charge			5		nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>.

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 1.65\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 14)	-	6	-	ns
$t_r$	Rise time		-	9.5	-	ns
$t_{d(off)}$	Turn-off-delay time		-	23	-	ns
$t_f$	Fall time		-	31	-	ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$I_{SD}$	Source-drain current		-		3.3	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		13.2	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 3.3\text{ A}$ , $V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 3.3\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 16)	-	200		ns
$Q_{rr}$	Reverse recovery charge		-	910		nC
$I_{RRM}$	Reverse recovery current		-	9.1		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 3.3\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$ (see Figure 16)	-	236		ns
$Q_{rr}$	Reverse recovery charge		-	1073		nC
$I_{RRM}$	Reverse recovery current		-	9.1		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

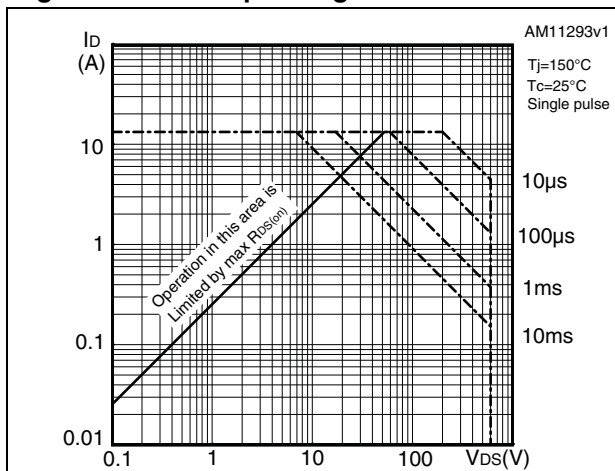


Figure 3. Thermal impedance

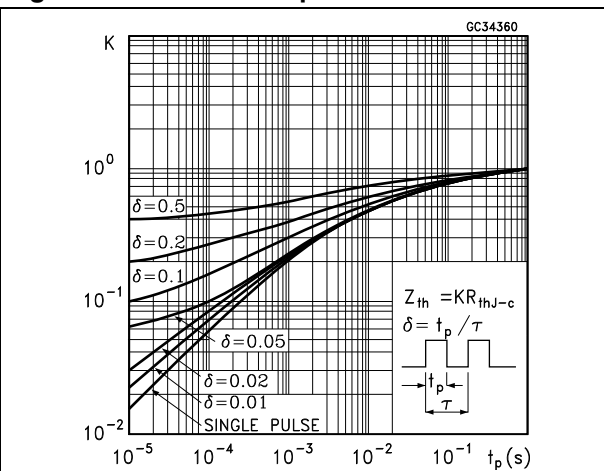


Figure 4. Output characteristics

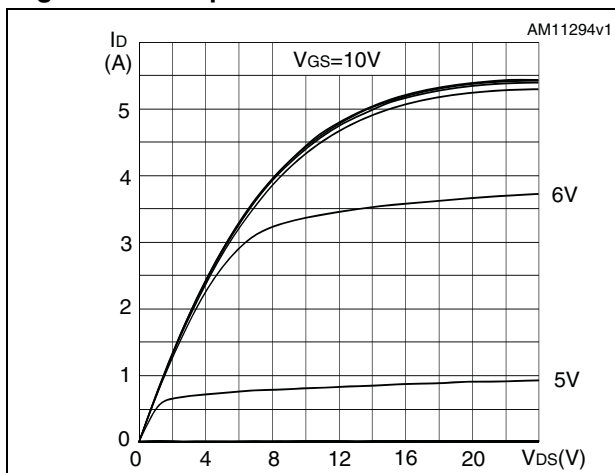


Figure 5. Transfer characteristics

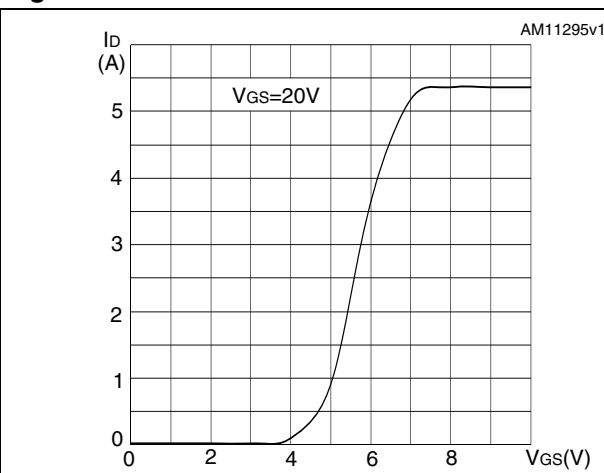


Figure 6. Gate charge vs gate-source voltage

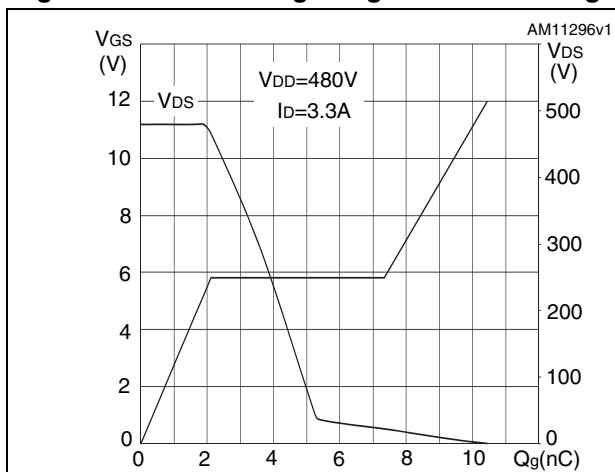


Figure 7. Static drain-source on-resistance

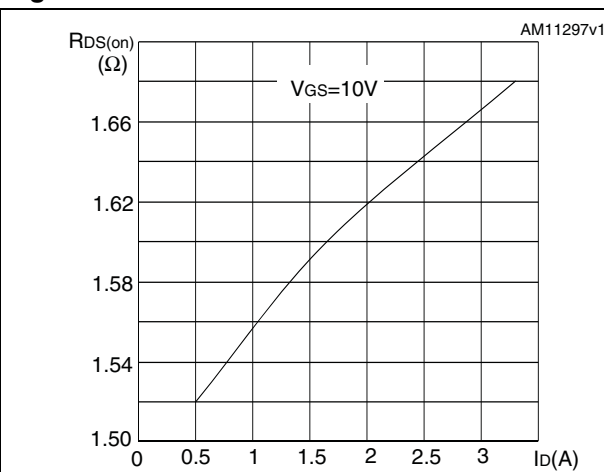


Figure 8. Capacitance variations

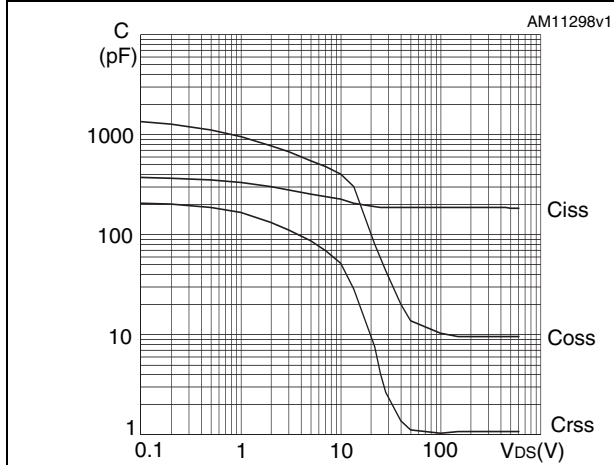


Figure 9. Output capacitance stored energy

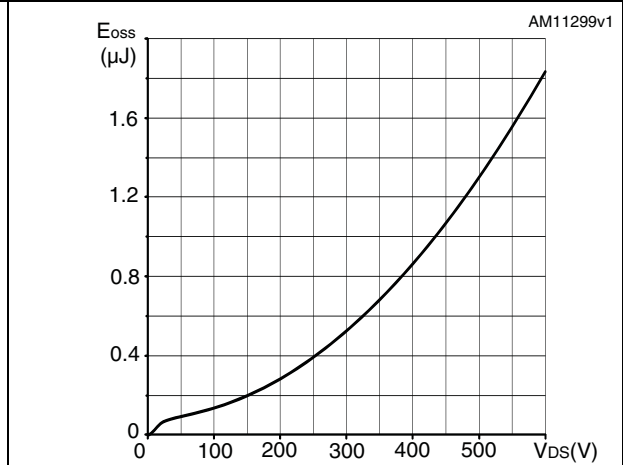


Figure 10. Normalized gate threshold voltage vs. temperature

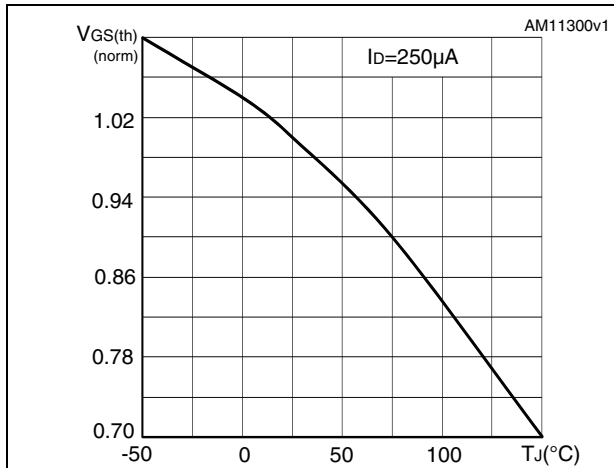


Figure 11. Normalized on-resistance vs. temperature

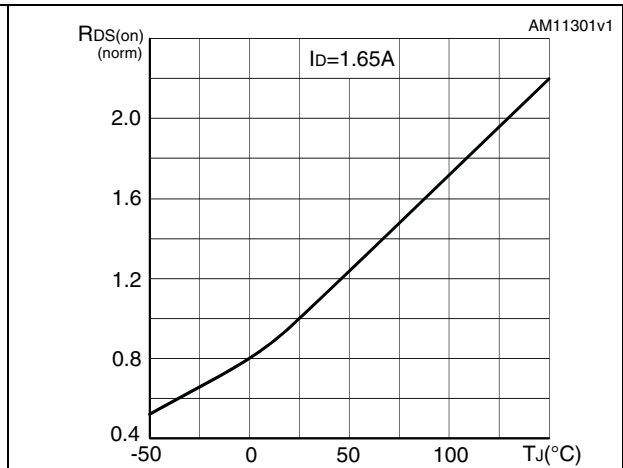


Figure 12. Source-drain diode forward characteristics

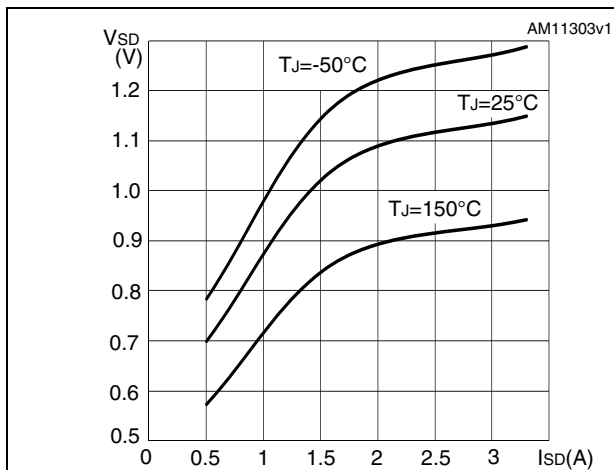
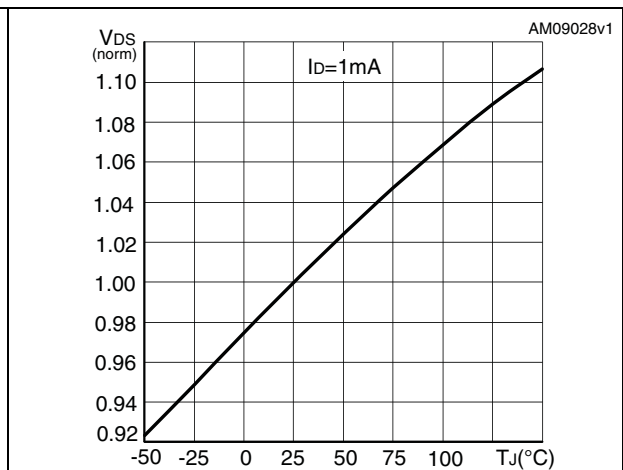


Figure 13. Normalized V<sub>DS</sub> vs. temperature

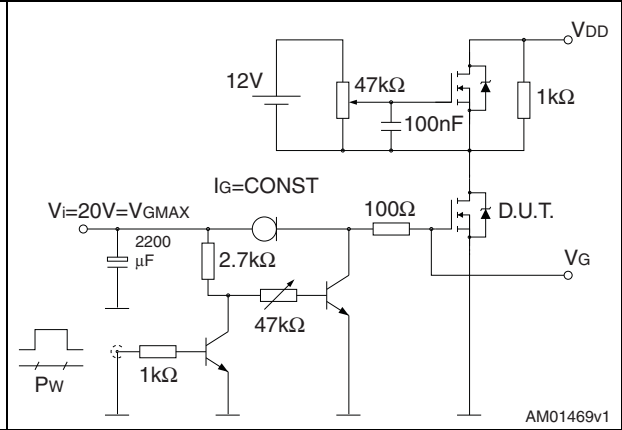


### 3 Test circuits

**Figure 14. Switching times test circuit for resistive load**



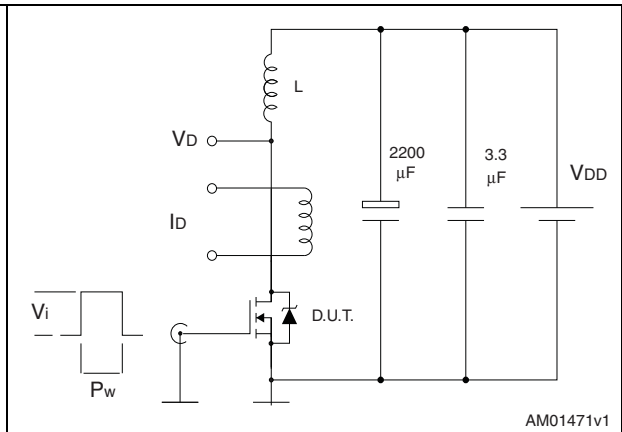
**Figure 15. Gate charge test circuit**



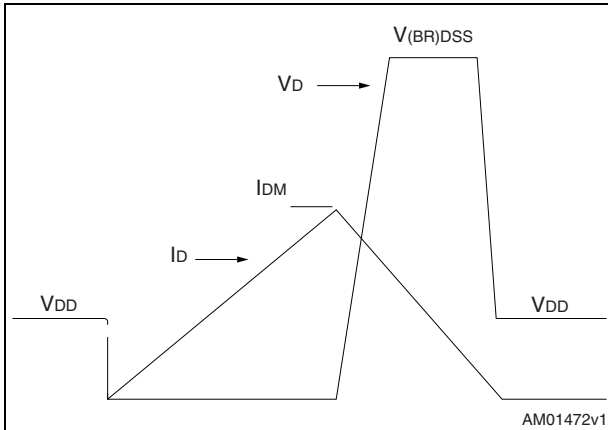
**Figure 16. Test circuit for inductive load switching and diode recovery times**



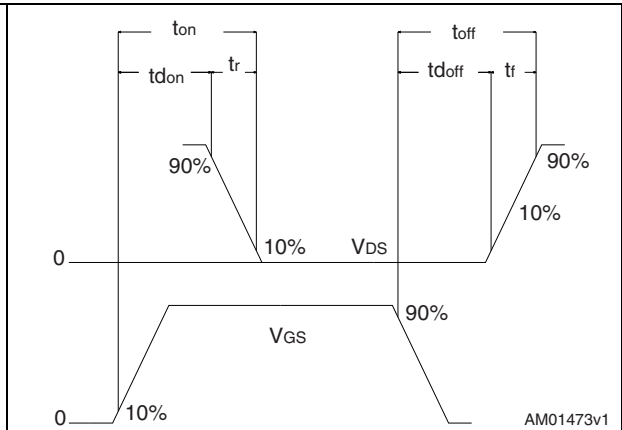
**Figure 17. Unclamped inductive load test circuit**



**Figure 18. Unclamped inductive waveform**



**Figure 19. Switching time waveform**





## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 9. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		1.50
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 20. DPAK (TO-252) drawing

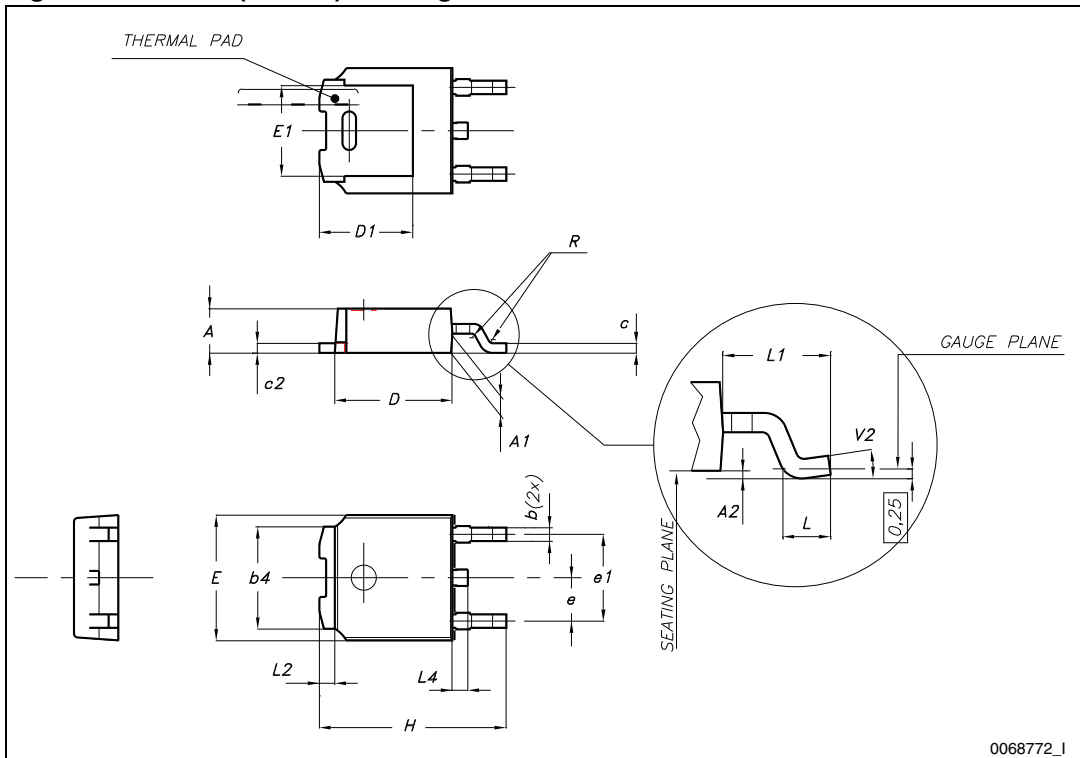
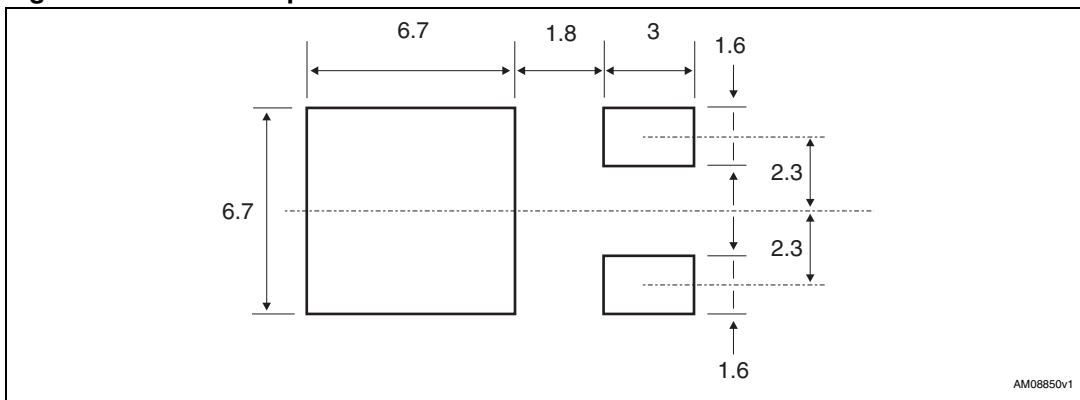


Figure 21. DPAK footprint<sup>(a)</sup>



a. All dimensions are in millimeters

## 5 Packaging mechanical data

Table 10. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 22. Tape for DPAK (TO-252)

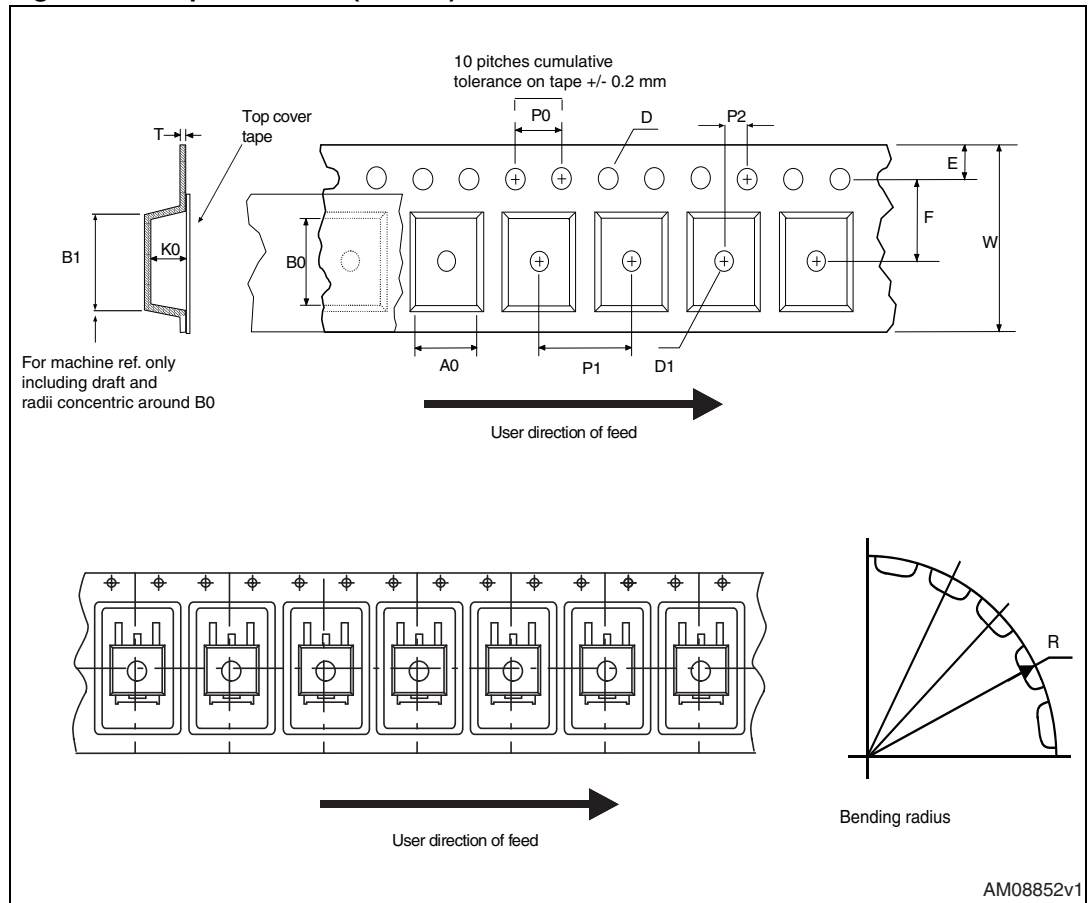
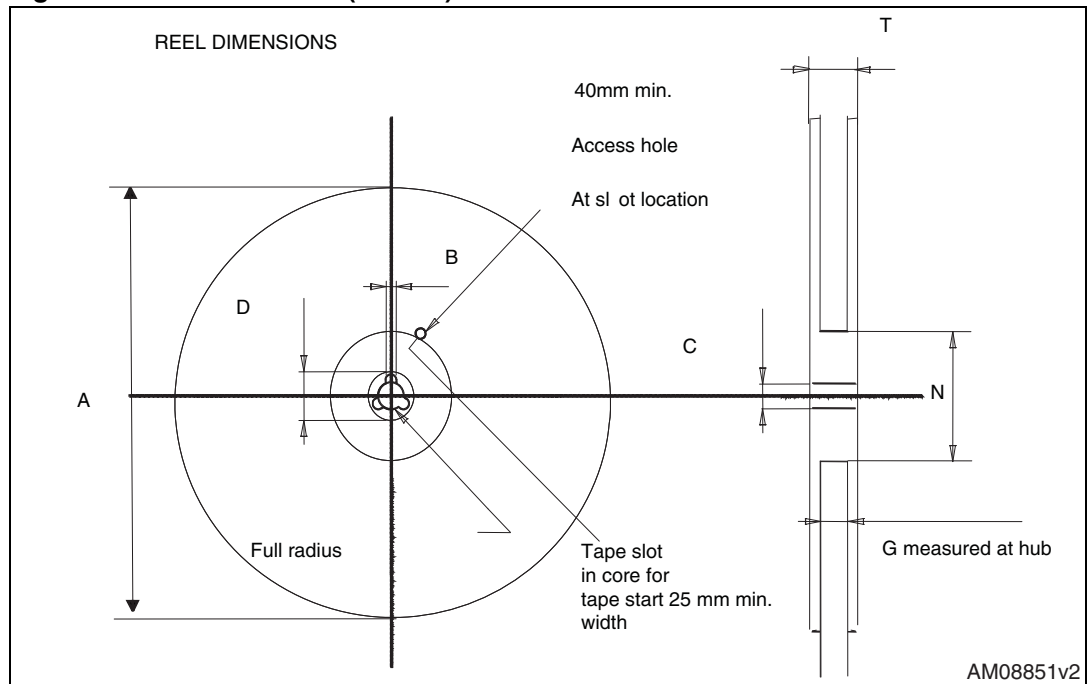


Figure 23. Reel for DPAK (TO-252)



## 6 Revision history

Table 11. Document revision history

Date	Revision	Changes
10-May-2012	1	First release

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